

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	5964	(@ad<"20021029" or @rlad<"20021029") and (((glass adj substrate) (insulat\$5 adj substrate))) and (pad terminal) and (substrate) and (device transistor tft) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) and (lcd "liquid crystal") and semiconductor	US-PGPUB; USPAT	OR	ON	2007/02/23 12:30
L7	172	(@ad<"20021029" or @rlad<"20021029") and (((pad adj pad) ("pad to pad"))) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:34
L8	6	(@ad<"20031002" or @rlad<"20031002") and (((pad adj pad) ("pad to pad"))) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not L7	US-PGPUB; USPAT	OR	ON	2007/02/23 12:36
L9	144	(@ad<"20021029" or @rlad<"20021029") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:37
L10	28	(@ad<"20031002" or @rlad<"20031002") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not L9	US-PGPUB; USPAT	OR	ON	2007/02/23 12:37

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L11	1907	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:40
L12	281	(@ad<"20031002" or @rlad<"20031002") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not L11	US-PGPUB; USPAT	OR	ON	2007/02/23 12:41
L13	588	(@ad<"20021029" or @rlad<"20021029") and 257/358, 360.ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:52
L14	55	(@ad<"20031002" or @rlad<"20031002") and 257/358, 360.ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) not L13	US-PGPUB; USPAT	OR	ON	2007/02/23 12:53
S1	1981	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 10:38
S2	1981	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/02/21 10:46
S3	1907	(@ad<"20021029" or @rlad<"20021029") and pad and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:40

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S4	144	(@ad<"20021029" or @rlad<"20021029") and pad and (guard adj ring) and (chip or substrate) and (protection adj device) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:36
S5	99	(@ad<"20021029" or @rlad<"20021029") and 257/487. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/21 13:06
S6	64	(@ad<"20021029" or @rlad<"20021029") and 257/489. ccls. and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:49
S7	57	("3676742" "3813639" "4331948" "4436183" "4486738" "4586105" "4726991" "4729752" "4770738" "4788523" "4813891" "4819047" "4928199" "4939619" "4945395" "4977357" "4992333" "5008770" "5029041" "5068634" "5089929" "5099380" "5101317" "5130881" "5142263" "5175662" "5183698" "5189387" "5194010" "5195010" "5197891" "5208723" "5216404" "5229037" "5246388" "5248517" "5260848" "5262754" "5278535" "5294374" "5301084" "5315472" "5340641" "5342220" "5393597" "5416662" "5444593" "5483407" "5515226" "5578867" "5674083" "5715127" "5796570").PN. OR ("6064094"). URP.N.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 13:12

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S8	44	((("3676742" "3813639" "4331948" "4436183" "4486738" "4586105" "4726991" "4729752" "4770738" "4788523" "4813891" "4819047" "4928199" "4939619" "4945395" "4977357" "4992333" "5008770" "5029041" "5068634" "5089929" "5099380" "5101317" "5130881" "5142263" "5175662" "5183698" "5189387" "5194010" "5195010" "5197891" "5208723" "5216404" "5229037" "5246388" "5248517" "5260848" "5262754" "5278535" "5294374" "5301084" "5315472" "5340641" "5342220" "5393597" "5416662" "5444593" "5483407" "5515226" "5578867" "5674083" "5715127" "5796570").PN. OR ("6064094"). URPN.) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric) and (@ad<"20021029" or @rlad<"20021029")	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 13:13
S9	3057	(@ad<"20021029" or @rlad<"20021029") and ((pad adj pad) ("pad to pad")) and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:22
S10	172	(@ad<"20021029" or @rlad<"20021029") and (((pad adj pad) ("pad to pad")) with (resistance resistor))and (resistance resistor) and (chip semiconductor terminal metal diode device transistor line layer substrate silicon first second electric)	US-PGPUB; USPAT	OR	ON	2007/02/23 12:34
S11	2	("5034796").PN. OR ("5635822"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/21 14:44
S12	9	("4982079").PN. OR ("5736732"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/22 08:35
S20	22	("4819047" "5173755" "5237395" "5641981").PN. OR ("5917220"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/02/22 16:14